The ZM220N03L combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

Trench technology

$_{DS(ON)}$ to minimize conductive loss

ge for fast switching

DC/DC Converters in Computing, Servers

Isolated DC/DC Converters in Telecom and Industrial

Product Summary

	REEL TAPE
	3000

T_C =25

Parameter	**Symbol**	Rating	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	12	V
Continuous Drain Current	$I_{D@}T_C$=25	5	A
	$I_{D@}T_C$=75	3.8	A
	$I_{D@}T_C$=100	3	A
Pulsed Drain Current	I_{DM}	15	A
Total Power Dissipation	$P_D@T_C$=25	18	W
Total Power Dissipation	$P_D@T_A$=25	0.9	W
Operating Junction Temperature	T_J	-55 to 150	
Storage Temperature	T_{STG}	-55 to 150	
Single Pulse Avalanche Energy@L=0.1mH	E_{AS}	5	mJ

Fig.1 Gate-Charge Characteristics

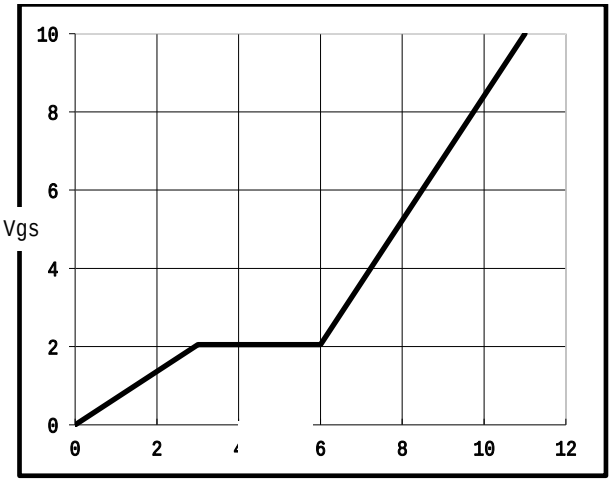


Fig.2 Capacitance Characteristics

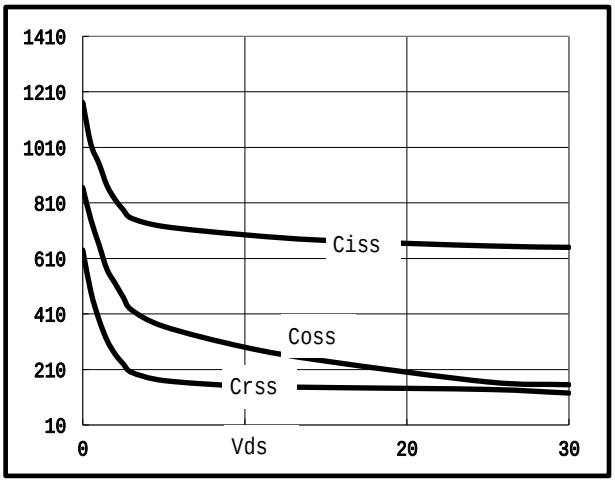


Fig.3 Power Dissipation Derating Curve

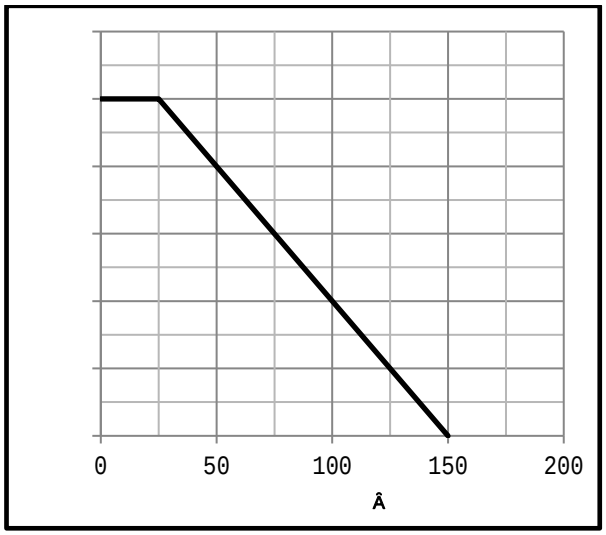


Fig.4 Typical output Characteristics

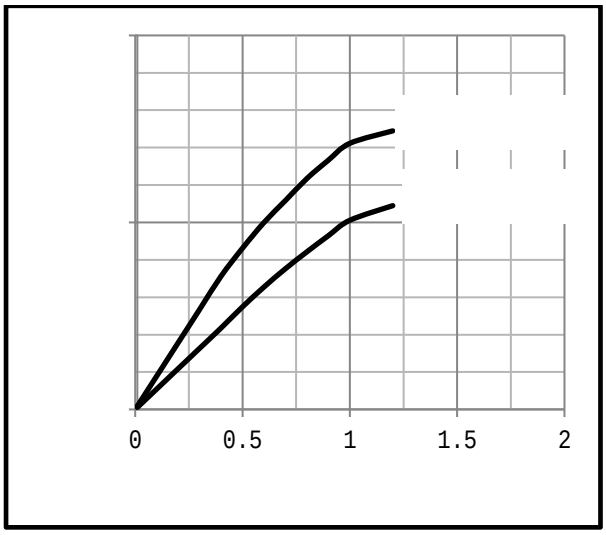


Fig.5 Threshold Voltage V.S Junction Temperature

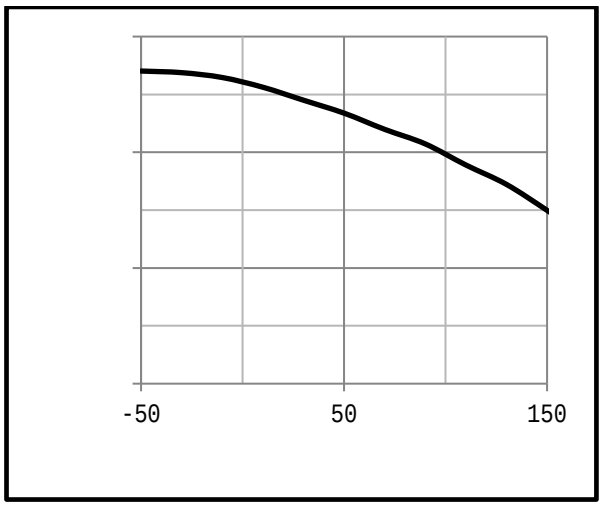
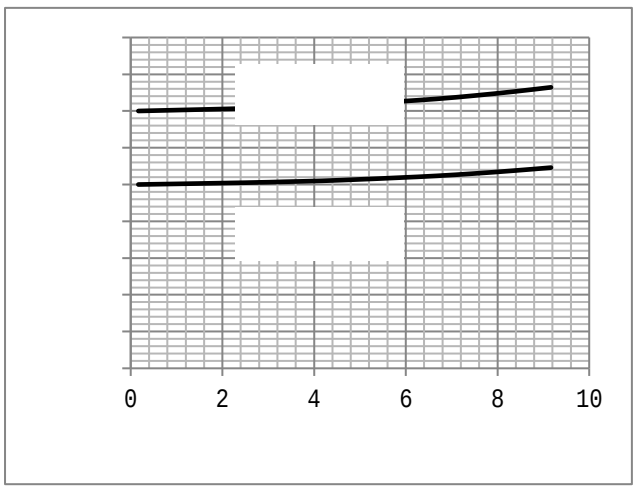
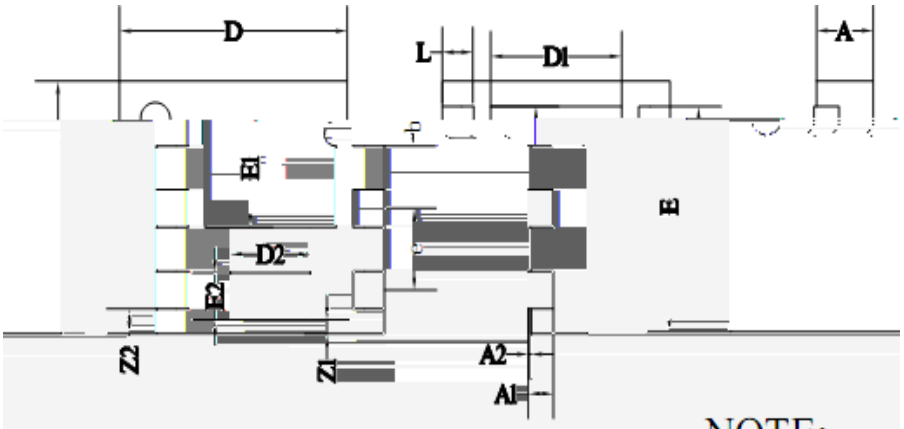


Fig.6 Resistance V.S Drain Current



(DFN2*2)

Unit mm



NOTE:

All dimens

	MIN	NOM	MAX
D	1.95	2.00	2.05
E	1.95	2.00	2.05
D1	1.10	1.15	1.20
E1	0.90	0.95	1.00
b	0.25	0.30	0.35
e		0.65	
L	0.25	0.30	0.35
A	0.45	0.50	0.55
A1			
A2		0.15	0.20
E2	0.45	0.50	0.55
b1	0.15	0.20	0.25